

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP560G

TRIAC DRIVER
PROGRAMMABLE CONTROLLERS
AC-OUTPUT MODULE
SOLID STATE RELAY

The TOSHIBA TLP560G consists of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

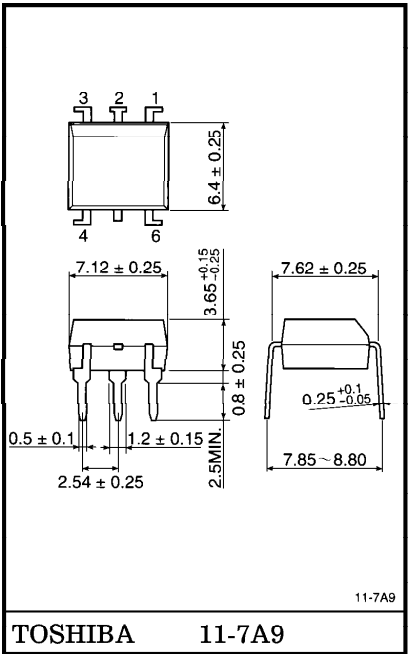
- Peak Off-State Voltage : 400V (MIN.)
- On-State Current : 100mA (MAX.)
- Isolation Voltage : 2500V_{rms} (MIN.)
- UL Recognized : File No. E67349
- Isolation Operating Voltage : 2500V_{ac} or 300V_{dc} for Isolation Groupe C*1
- Trigger LED Current

CLASSI- FICATION*	TRIGGER LED CURRENT (mA)		MARKING OF CLASSIFICATION
	V _T =6V, T _a =25°C		
	MIN.	MAX.	
(IFT5)	—	5	T5
(IFT7)	—	7	T5, T7
Standard	—	10	T5, T7, Blank

*Ex. (IFT5) ; TLP560G (IFT5)
(Note) Application type name for certification test, please use standard product type name, i.e.
TLP560G (IFT5) : TLP560G

*1 : According to VDE0110, table 4.

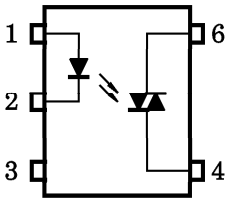
Unit in mm



TOSHIBA 11-7A9

Weight : 0.39g

PIN CONFIGURATION (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : TERMINAL 1
- 6 : TERMINAL 2

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current		I _F	50	mA
	Forward Current Derating (Ta≥ 53°C)		ΔI _F / °C	−0.7	mA / °C
	Peak Forward Current (100μs pulse, 100pps)		I _{FP}	1	A
	Reverse Voltage		V _R	5	V
	Junction Temperature		T _j	125	°C
DETECTOR	Off-State Output Terminal Voltage		V _{DRM}	400	V
	On-State RMS Current	Ta= 25°C	I _T (RMS)	100	mA
		Ta= 70°C		50	
	On-State Current Derating (Ta≥ 25°C)		ΔI _T / °C	−1.1	mA / °C
	Peak On-State Current (100μs pulse, 120pps)		I _{TP}	2	A
	Peak Nonrepetitive Surge Current (Pw= 10ms, DC= 10%)		I _{TSM}	1.2	A
	Junction Temperature		T _j	115	°C
	Storage Temperature Range		T _{stg}	−55~125	°C
Operating Temperature Range		T _{opr}	−40~100	°C	
Lead Soldering Temperature (10s)		T _{sol}	260	°C	
Isolation Voltage (AC, 1 min., R.H.≤ 60%)		BV _S	2500	V _{rms}	

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{AC}	—	—	120	V _{ac}
Forward Current	I _F	15	20	25	mA
Peak On-State Current	I _{TP}	—	—	1	A
Operating Temperature	T _{opr}	−25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	10	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	$V_{\text{DRM}} = 400\text{V}$	—	10	100	nA
	Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{\text{in}} = 120\text{V}_{\text{rms}}, T_a = 85^\circ\text{C}$ (Fig.1)	200	500	—	$\text{V} / \mu\text{s}$
	Critical Rate of Rise of Commutating Voltage	$dv/dt(c)$	$V_{\text{in}} = 30\text{V}_{\text{rms}}, I_T = 15\text{mA}$ (Fig.1)	—	0.2	—	$\text{V} / \mu\text{s}$

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	$V_T = 3\text{V}$	—	5	10	mA
Capacitance (Input to Output)	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}$	5×10^{10}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	2500	—	—	V_{rms}
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	V_{dc}

Fig.1 : dv / dt TEST CIRCUIT

